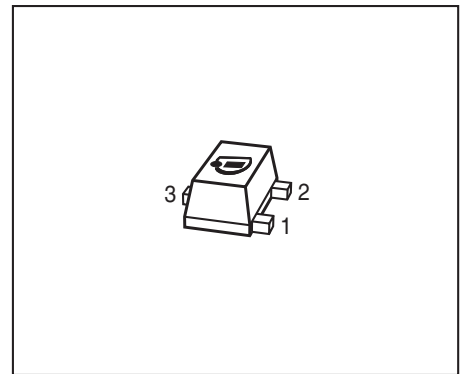


NPN Silicon RF Transistor

- Low noise amplifier for low current applications
- Collector design supports 5V supply voltage
- For oscillators up to 3.5 GHz
- Low noise figure 1.0 dB at 1.8 GHz
- Pb-free (RoHS compliant) package
- Qualified according AEC Q101



ESD (Electrostatic discharge) sensitive device, observe handling precaution!

Type	Marking	Pin Configuration			Package
BFR360F	FBs	1 = B	2 = E	3 = C	TSFP-3

Maximum Ratings at $T_A = 25\text{ }^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Value	Unit
Collector-emitter voltage	V_{CEO}	6	V
Collector-emitter voltage	V_{CES}	15	
Collector-base voltage	V_{CBO}	15	
Emitter-base voltage	V_{EBO}	2	
Collector current	I_C	35	mA
Base current	I_B	4	
Total power dissipation ¹⁾ $T_S \leq 98\text{ }^\circ\text{C}$	P_{tot}	210	mW
Junction temperature	T_J	150	$^\circ\text{C}$
Storage temperature	T_{Stg}	-55 ... 150	

Thermal Resistance

Parameter	Symbol	Value	Unit
Junction - soldering point ²⁾	R_{thJS}	≤ 250	K/W

¹⁾ T_S is measured on the collector lead at the soldering point to the pcb

²⁾ For calculation of R_{thJA} please refer to Application Note AN077 Thermal Resistance

Electrical Characteristics at $T_A = 25^\circ\text{C}$, unless otherwise specified

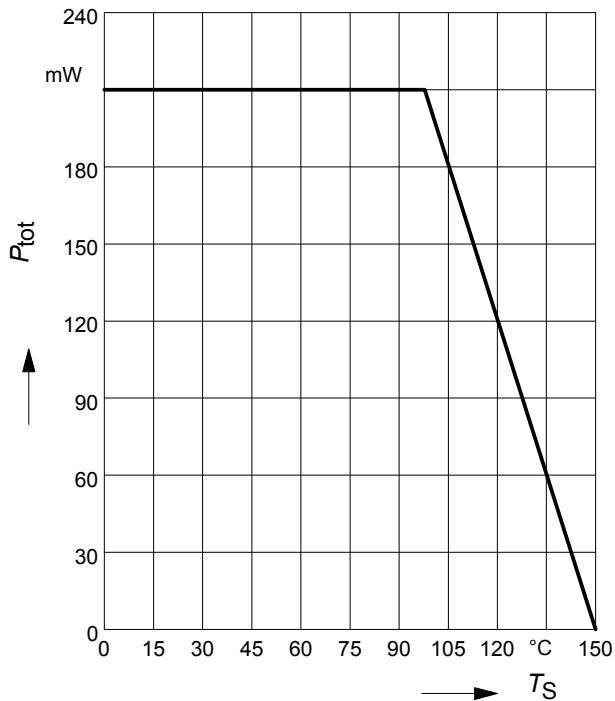
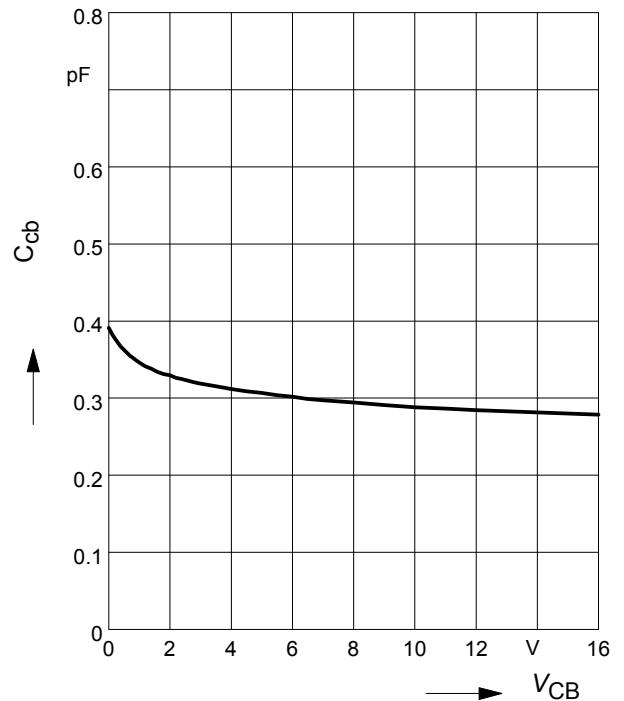
Parameter	Symbol	Values			Unit
		min.	typ.	max.	
DC Characteristics					
Collector-emitter breakdown voltage $I_C = 1\text{ mA}, I_B = 0$	$V_{(BR)CEO}$	6	9	-	V
Collector-emitter cutoff current $V_{CE} = 4\text{ V}, V_{BE} = 0$ $V_{CE} = 10\text{ V}, V_{BE} = 0, T_A = 85^\circ\text{C}$ Verified by random sampling	I_{CES}	-	1 2	30 50	nA
Collector-base cutoff current $V_{CB} = 4\text{ V}, I_E = 0$	I_{CBO}	-	1	30	
Emitter-base cutoff current $V_{EB} = 1\text{ V}, I_C = 0$	I_{EBO}	-	1	500	
DC current gain $I_C = 15\text{ mA}, V_{CE} = 3\text{ V}$, pulse measured	h_{FE}	90	120	160	-

Electrical Characteristics at $T_A = 25^\circ\text{C}$, unless otherwise specified

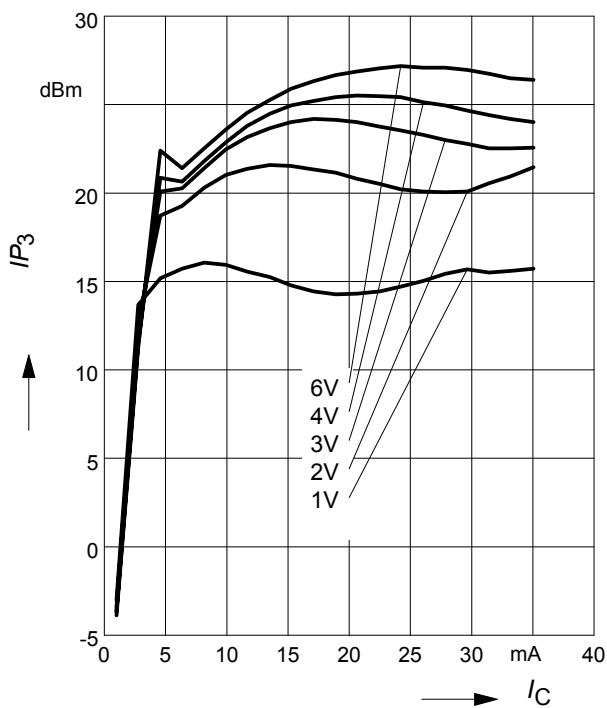
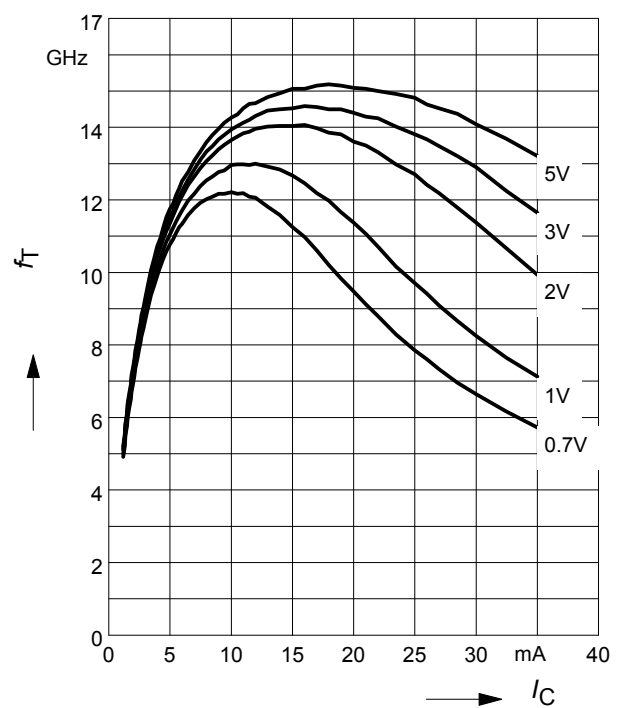
Parameter	Symbol	Values			Unit
		min.	typ.	max.	
AC Characteristics (verified by random sampling)					
Transition frequency $I_C = 15\text{ mA}$, $V_{CE} = 3\text{ V}$, $f = 1\text{ GHz}$	f_T	11	14	-	GHz
Collector-base capacitance $V_{CB} = 5\text{ V}$, $f = 1\text{ MHz}$, $V_{BE} = 0$, emitter grounded	C_{cb}	-	0.32	0.5	pF
Collector emitter capacitance $V_{CE} = 5\text{ V}$, $f = 1\text{ MHz}$, $V_{BE} = 0$, base grounded	C_{ce}	-	0.2	-	
Emitter-base capacitance $V_{EB} = 0.5\text{ V}$, $f = 1\text{ MHz}$, $V_{CB} = 0$, collector grounded	C_{eb}	-	0.4	-	
Minimum noise figure $I_C = 3\text{ mA}$, $V_{CE} = 3\text{ V}$, $Z_S = Z_{Sopt}$, $f = 1.8\text{ GHz}$	NF_{min}	-	1	-	dB
Power gain, maximum available ¹⁾ $I_C = 15\text{ mA}$, $V_{CE} = 3\text{ V}$, $Z_S = Z_{Sopt}$, $Z_L = Z_{Lopt}$, $f = 1.8\text{ GHz}$ $f = 3\text{ GHz}$	G_{ma}	- -	15.5 11	- -	
Transducer gain $I_C = 15\text{ mA}$, $V_{CE} = 3\text{ V}$, $Z_S = Z_L = 50\Omega$, $f = 1.8\text{ GHz}$ $f = 3\text{ GHz}$	$ S_{21e} ^2$	- -	13 9	- -	dB
Third order intercept point at output ²⁾ $V_{CE} = 3\text{ V}$, $I_C = 15\text{ mA}$, $f = 1.8\text{ GHz}$, $Z_S = Z_L = 50\Omega$	IP_3	-	24	-	dBm
1dB compression point at output $I_C = 15\text{ mA}$, $V_{CE} = 3\text{ V}$, $Z_S = Z_L = 50\Omega$, $f = 1.8\text{ GHz}$	P_{-1dB}	-	9	-	

$$^1G_{ma} = |S_{21e}| / |S_{12e}| (k - (k^2 - 1)^{1/2})$$

² IP_3 value depends on termination of all intermodulation frequency components.
Termination used for this measurement is 50Ω from 0.1 MHz to 6 GHz

Total power dissipation $P_{tot} = f(T_S)$

**Collector-base capacitance $C_{cb} = f(V_{CB})$
 $f = 1\text{MHz}$**

Third order Intercept Point $IP_3 = f(I_C)$

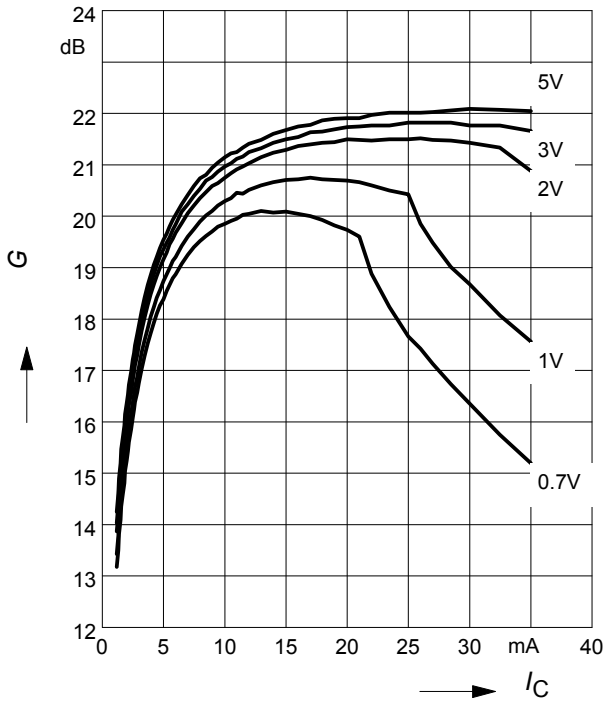
 (Output, $Z_S = Z_L = 50\Omega$)

 $V_{CE} = \text{parameter}, f = 1.8\text{GHz}$

Transition frequency $f_T = f(I_C)$
 $f = 1\text{GHz}$
 $V_{CE} = \text{parameter}$


Power gain G_{ma} , $G_{ms} = f(I_C)$

$f = 0.9\text{GHz}$

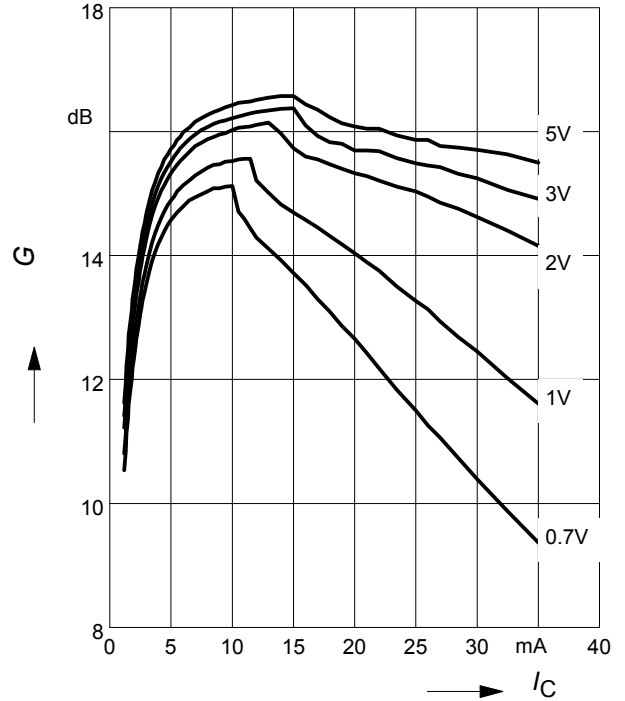
$V_{CE} = \text{parameter}$



Power gain G_{ma} , $G_{ms} = f(I_C)$

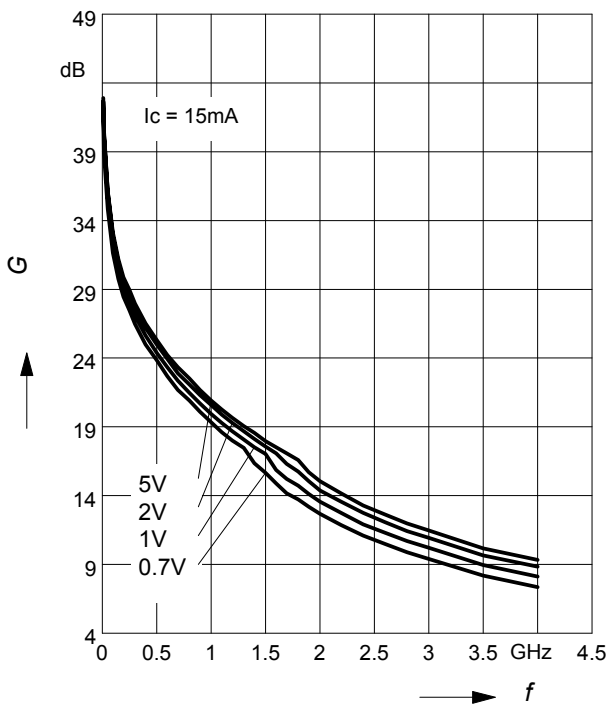
$f = 1.8\text{GHz}$

$V_{CE} = \text{parameter}$



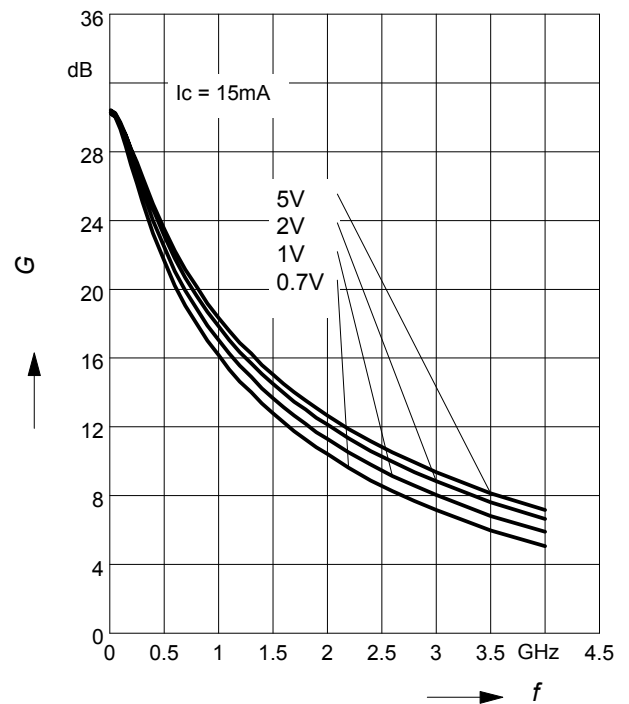
Power Gain G_{ma} , $G_{ms} = f(f)$

$V_{CE} = \text{parameter}$



Insertion Power Gain $|S_{21}|^2 = f(f)$

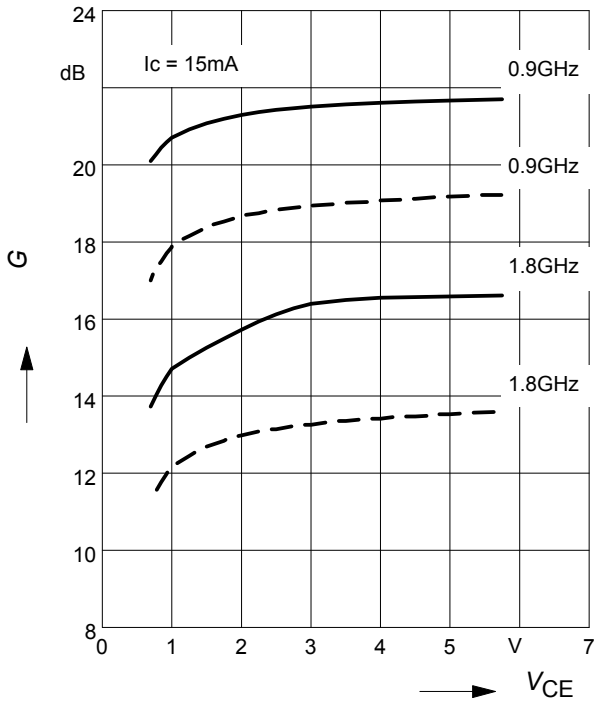
$V_{CE} = \text{parameter}$



Power Gain $G_{ma}, G_{ms} = f(V_{CE})$: —

$|S_{21}|^2 = f(V_{CE})$: - - - -

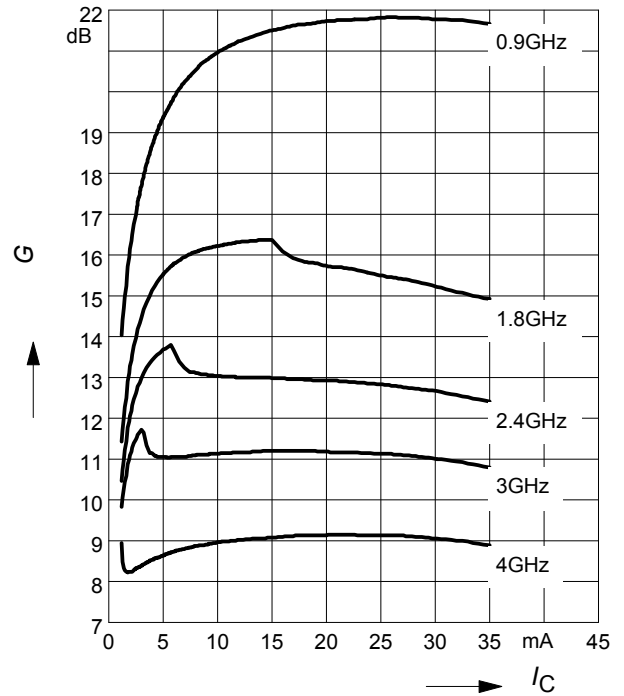
f = parameter



Power gain $G_{ma}, G_{ms} = f(I_C)$

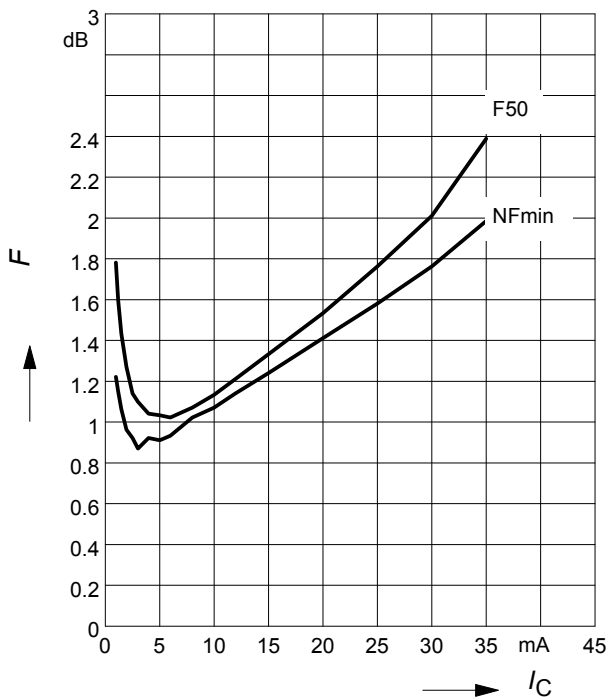
$V_{CE} = 3V$

f = parameter



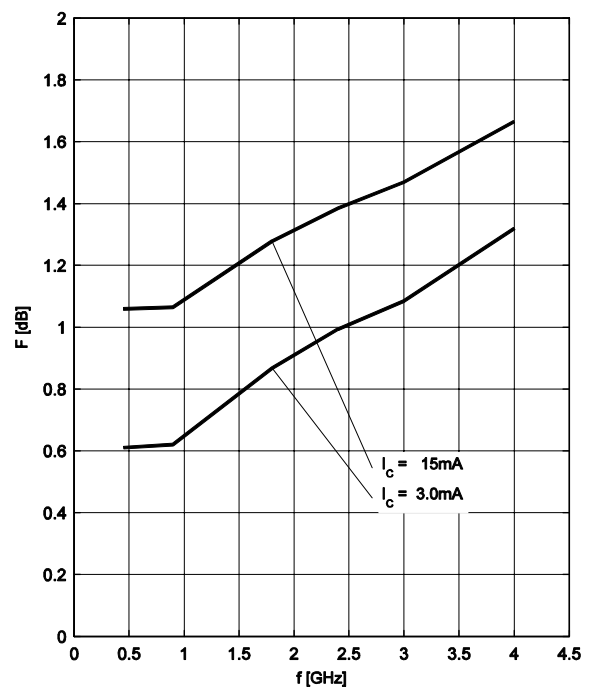
Noise figure $NF = f(I_C)$

$V_{CE} = 3V, f = 1,8 \text{ GHz}$



Noise figure $F = f(f)$

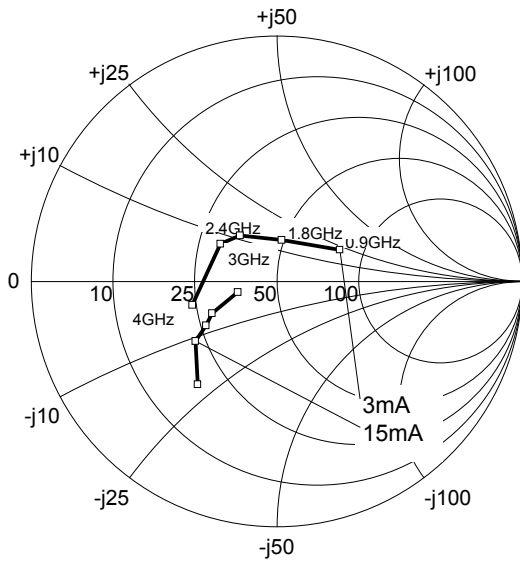
$V_{CE} = 3V, Z_S = Z_{Sopt}$



Source impedance for min.

noise figure vs. frequency

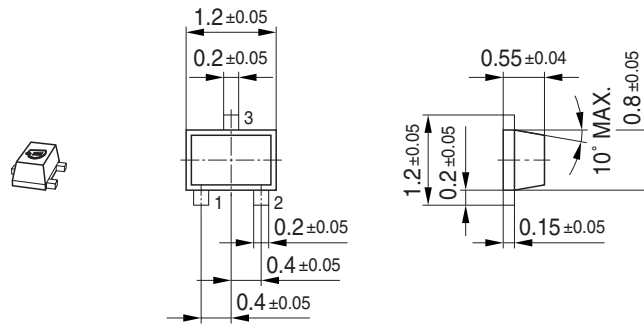
$V_{CE} = 3\text{ V}$



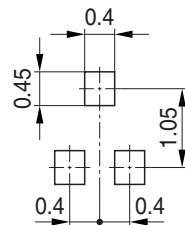
SPICE Parameter

For the SPICE model as well as for the S-parameters (including noise parameters) please refer to our internet website www.infineon.com/rf.models.

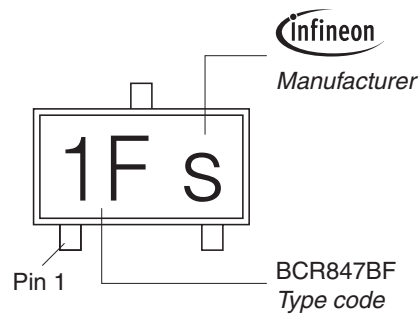
Package Outline



Foot Print



Marking Layout (Example)



Standard Packing

Reel \varnothing 180 mm = 3.000 Pieces/Reel
 Reel \varnothing 330 mm = 10.000 Pieces/Reel



Datasheet Revision History: 20 May 2010

This datasheet replaces the revision from 30 March 2007.

The product itself has not been changed and the device characteristics remain unchanged. Only the product description and information available in the datasheet has been expanded and updated.

Previous Revision: 30 March 2007	
Page	Subject (changes since last revision)
1	Datasheet has final status
1	Max. ratings refer to 25°C
1	Max. rating for T_A removed
1	Lower max. rating for storage temperature T_{Stg} changed
2	Typical values for leakage currents included, maximum leakage current values reduced
6	Characteristic curve for NFmin vs. frequency included

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